

Title (en)
IN SITU GETTER PUMP SYSTEM AND METHOD

Title (de)
IN-SITU GETTERPUMPSYSTEM UND VERFAHREN

Title (fr)
SYSTEME DE POMPE GETTER IN SITU ET METHODE

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Application
EP 98915555 A 19980415

Priority
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Abstract (en)
[origin: WO9848168A2] A wafer processing system including a processing chamber, a low pressure pump coupled to the processing chamber for pumping noble and non-noble gases, a valve mechanism coupling a source of noble gas to the processing chamber, an in situ getter pump disposed within the processing chamber which pumps certain non-noble gases during the flow of the noble gas into the chamber, and a processing mechanism for processing a wafer disposed within the processing chamber. Preferably, the in situ getter pump can be operated at a number of different temperatures to preferentially pump different species of gas at those temperatures. A gas analyzer is used to automatically control the temperature of the getter pump to control the species of gasses that are pumped from the chamber. An alternate embodiment of the invention includes an in situ getter pump additionally provided within the transfer chamber of the semiconductor manufacturing equipment.

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